### Topic VII

2/5:

## Band Theory in Solids

#### VII.1 Module 21: Electronic Structure of Solids (1D Solids)

- Solid silicon's symmetry space group would be  $Fd\overline{3}m$ .
  - Suggested reading: Hoffmann (1987).
  - To consider solids, let's first consider an infinite chain of hydrogen atoms.
    - This should separate into H<sub>2</sub> molecules (**Peierl's instability**).
    - However, other substances can have chains of  $p_z$  orbitals, such as platinum atoms.
  - An imaginary zoo of hydrogen molecules (we use the limit of a cycle of hydrogen atoms to approximate an infinitely long chain):
    - H<sub>2</sub> has a bonding and antibonding MO.
    - Cyclic  ${\rm H_3}^+$  is the most abundant ion in the universe (recently discovered by UChicago). One bonding and two antibonding orbitals.
    - We can keep adding hydrogen atoms to our rings.
    - For an infinitely long cycle of hydrogen atoms, we will have an infinite number of states close together that resembles a band in solids.
  - Back to the chain of H atoms:
    - The basis function on each lattice point is a  $H_{1s}$  orbital.
    - The appropriate SALC  $\psi$  is

$$\psi_k = \sum_n e^{ikna} \phi_n$$

- In this formalism, k is an index labeling irreducible representations of the translation group.  $\psi$  transforms just like a,  $e_1$ , and  $e_2$  (e.g., in the  $C_5$  point symmetry group).
- This process of symmetry adaptation is called "forming Bloch functions."
- Elementary band theory for extended solids:
  - Energy bands in solids arise from overlapping atomic orbitals, which become the **crystal orbitals** that make up the bands.
  - Recipe: Use LCAO (tight binding) approach.
  - A crystal is a regular periodic array with translational symmetry.
  - Periodic boundary conditions require  $\psi(x+Na) = \psi(x)$ , i.e., each wavefunction must be symmetry equivalent to the one in the neighboring cells.

- For a 1D solid with lattice constant a and atom index n, **Bloch's theorem** tells us that the above SALC  $\psi_k$  is a solution to the Schrödinger equation.
- If we calculate  $\psi_0$  and  $\psi_{\pi/a}$ , we get the most and least bonding states possible, respectively (the least bonding state is the most antibonding state and has the highest energy).



Figure VII.1: s orbital bonding states.

$$\psi_0 = \phi_0 + \phi_1 + \phi_2 + \phi_3 + \cdots$$
$$\psi_{\pi/a} = \phi_0 - \phi_1 + \phi_2 - \phi_3 + \cdots$$

- At this point, we can construct a band between these two states. picture
  - The band is *almost* infinite; it's on the order of Avogadro's number.
  - We have as many k values as translations in the crystal or as many unit cells in a crystal.

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- First Brillouin zone: The region that covers all possible energy states that the crystal can have.
  - It is  $-\frac{\pi}{a} < k < \frac{\pi}{a}$ ; which is the range of all possible values that the sine function will give.
- There is one energy level for each value of k, but E(k) = E(-k).
- The energy is proportional to the electron momentum.
- Calculation of 1D band structure:
  - We have N atoms such that  $\psi_k = \sum_{n=0}^N e^{inka} \phi_n$ .
  - The crystal Schrödinger equation is  $\hat{H}\Psi(k) = E(k)\Psi(k)$ .
  - Thus, the electron energies are given by

$$E(k) = \frac{\langle \psi | \hat{H} | \psi \rangle}{\langle \psi | \psi \rangle}$$

– Recall that in Dirac's bra-ket notation,  $\langle \psi | \hat{H} | \psi \rangle \equiv \int \psi^* \hat{H} \psi \, d\tau$ ; for normalized atomic orbitals and ignoring overlap integrals:

$$\langle \phi_m | \phi_n \rangle = \begin{cases} 1 & m = n \\ 0 & m \neq n \end{cases}$$

- Also recall that

$$\langle \psi | \psi \rangle = \sum_{m,n} e^{i(n-m)ka} \langle \phi_m | \phi_n \rangle = N$$

- Thus, we can calculate for on-site (m = n):

$$\langle \psi(k)|\hat{H}|\psi(k)\rangle = \sum_{n} \langle \phi_{n}|\hat{H}|\phi_{n}\rangle = N\alpha$$

And for resonance  $(m \neq n)$ , where we need only consider the two nearest neighbors:

$$\left\langle e^{-inka}\phi_n \middle| \hat{H} \middle| e^{i(n\pm 1)ka}\phi_{n\pm 1} \right\rangle = \beta e^{\pm ika}$$

- Putting everything together, we have

$$E(k) = \frac{\langle \psi | \hat{H} | \psi \rangle}{\langle \psi | \psi \rangle} = \frac{N\alpha + N\beta (e^{ika} + e^{-ika})}{N} = \alpha + 2\beta \cos(ka)$$

- **Zone center**: The ? where all atomic orbitals are in phase (all bonding  $\sigma$ ). Also known as  $\Gamma$ .
- Zone border: The ? where all atomic orbitals are out of phase (all antibonding  $\sigma^*$ ). Also known as X.
- Large numbers of MOs form bands of states.
- Band structure: The plot of E as a function of k.
  - The one we've derived so far is an s-shape curve.
- The p-orbitals are opposite they form a bonding state with inverted phases.



Figure VII.2: p orbital bonding states.

- The analysis of Figures VII.1 and VII.2 can be done for many more types of orbitals, including  $p_z$ ,  $d_{z^2}$ , and  $d_{xz}$ .
- Bonding orbital bands run uphill (concave upwards E(k)) at k=0 and antibonding orbital bands run downhill (concave downwards E(k)) at k=0.
- Energy bands run from  $\alpha + 2\beta$  to  $\alpha 2\beta$  since  $\beta$  is negative for s orbitals.
- Density of states: The number of energy levels in the energy interval  $\Delta E$ . Also known as DOS.

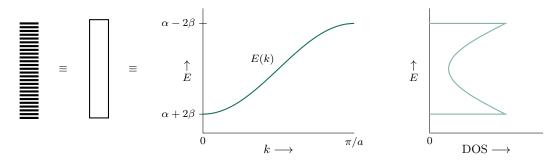


Figure VII.3: Density of states.

- Proportional to the inverse slope of the band; steep bands with large overlap yield a small DOS, and vice versa for flat bands.
- Reality check: PES for a long-chain alkane  $(C_{36}H_{74})$  shows this inverse DOS relationship for a little while.

# VII.2 Module 22: Electronic Structure of Solids (2D and 3D solids)

- 2D band structure:
  - Simple Hückel: A two-dimensional square net (s orbitals only (or  $p_z$ )).

$$\psi(k) = \sum_{m,n} e^{ik_x ma + ik_y na} \cdot \phi_{m,n}$$

- Consider the **crystal orbitals** at special k points (high symmetry).
- The **Brillouin zone** is 2D here (we have a **wave vector**).

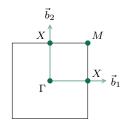


Figure VII.4: 2D Brillouin zone.

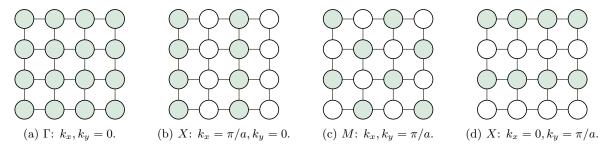


Figure VII.5: Special k points.

- The center is the  $\Gamma$  point  $(k_x = k_y = 0)$ . The midpoint of the lines are called X points  $(k_x = \frac{\pi}{a}, k_y = 0, \text{ and vice versa})$ . The maximum point is the M point  $(k_x = k_y = \frac{\pi}{a})$ .
- Calculating E(k) in two dimensions.

$$E(k) = \alpha + 2\beta(\cos(k_x a) + \cos(k_u a))$$

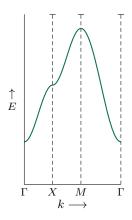


Figure VII.6: Schematic band structure (2D).

- Our schematic band structure (Figure VII.6) traces a 2D path  $\Gamma \to X \to M \to \Gamma$ .
- The bandwidth  $4|\beta|$  is proportional to the degree of interaction between neighboring orbitals.
  - Since  $\beta$  is the interaction integral and E(k) varies from  $\alpha 2\beta$  to  $\alpha + 2\beta$ .
- For  $p_{\sigma}$  orbitals,  $\beta > 0$ .

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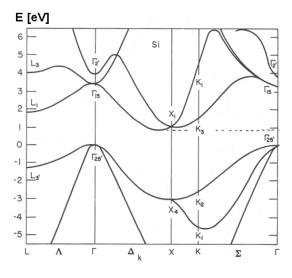
- Deriving the density of states formula:
  - We often simplify E(k) with the first term of the Taylor series expansion; this gives us

$$E = \frac{\hbar}{2m}k^2$$

- This implies that  $E \propto k^2$  and, hence,  $k \propto \sqrt{E}$ .
- Thus, the one-dimensional density  $D_{1d}(k)$  of states as a function of k is dN(k)/dk = 1 since the number of states is evenly distributed along the k axis (i.e., in Figure VII.3).
- It follows that the one-dimensional density  $D_{1d}(E)$  of states as a function of E is

$$D_{1d}(E) = \frac{\mathrm{d}N(E)}{\mathrm{d}E} = \frac{\mathrm{d}N(k)}{\mathrm{d}k} \frac{\mathrm{d}k}{\mathrm{d}E} \propto 1 \cdot \frac{1}{\sqrt{E}} = \frac{1}{\sqrt{E}}$$

- For each orbital, there is a unique path akin to Figure VII.6. The combination of all of these **bands** in one graph characterizes a material.
- Wigner-Seitz cell (of the reciprocal lattice): The first Brillouin zone, or FBZ.
  - A primitive cell with a lattice point at its center.
  - A 3D discrete Fourier transform of the lattice.
  - Has  $k_{x,y,z}$ .
  - What is "d.I." and "r.I."?
  - We once again can find high symmetry points and directions akin to those in Figure VII.4.



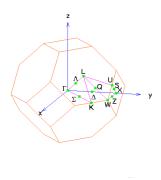


Figure VII.7: Electronic band structure of Si.

• Electronic band structure is calculated within the first Brilluoin zone to give us the electronic band structure of a solid.

- Angle-resolved photoemission spectroscopy<sup>[1]</sup>: If the incoming photon's energy is greater than the electron's ginding energy, the electron will eventually be emitted with a characteristic kinetic energy and angle relative to the surface normal. This angle is related to the electron's crystal momentum. The Bloch wave vector is linked to the measured electron's momentum. Also known as ARPES.
  - Indeed, ARPES can be used to reconstruct the band structure of a solid. The bands are real!

#### VII.3 Module 23: Filling Bands With Electrons

- The Fermi-Dirac statistics and Fermi Energy:
  - At T=0, we expect all of the atoms in a solid to be in the ground state. The distribution of electrons (fermions) at the various energy levels is governed by the Fermi-Dirac distribution:

$$F(E) = \frac{1}{1 + \exp\left(\frac{E - E_F}{kT}\right)}$$

where  $E_F$  is the Fermi energy.

- $\blacksquare$  F(E) is the probability to fill the states with a given energy E.
- When T = 0 K, the Fermi energy is the energy of the last occupied state. Moreover,
- The Fermi energy is the energy of the last occupied state at  $T=0\,\mathrm{K}$ ; it is proportional to the square of the Fermi state  $k_F$ , i.e.,  $E_F \propto k_F^2$ .
- If T > 0, then:
  - We fill the states from bottom to top.
  - Instead of having a sharp shift from occupied to unoccupied states, we have a sort-of washed-out step function.
  - Far below  $E_F$ , F(E) = 1; far above  $E_F$ , F(E) = 0. In the small **Fermi window** (aka. **Fermi level**) at the border (where the washed-out step function is), 0 < F(E) < 1.
    - The Fermi window is 4kbt.
  - It is in the Fermi level that all of the important stuff happens (i.e., electrons flowing in metals).
- If the gap (range where DOS(E) = 0) in the density of states at the Fermi level is smaller than 3 eV, then we have a semiconductor. If larger, we have an insulator. If 0, we have a conductor. Magnitude of DOS at Fermi level correlates with conductivity (e.g., Al has a higher DOS at the Fermi level than Ag, and we observe that Al is more conductive than Ag).
  - In metals and insulators, the Fermi level is within bands.
  - In semiconductors, it is between bands.
  - In physics, everything is a metal or insulator; semiconductors are a constructed perspective.
- Fermi sphere:
  - The surface of the Fermi sphere separates occupied and unoccupied states in k-space.
  - Bounded by Fermi surface.
  - Radius is Fermi wave vector  $k_F = \sqrt[3]{3\pi^2 n}$  where n is a parameter related to the density of electrons.
  - Fermi energy:  $E_F = \hbar^2 k_F^2 / 2m$ .
  - Fermi momentum:  $p_F = \hbar k_F$ .
  - Fermi velocity:  $v_F = \hbar k_F/m$ .

<sup>&</sup>lt;sup>1</sup>Figure 7.20 in Labalme (2020) actually refers to this kind of photoelectron spectroscopy!

- Fermi temperature:  $T_F = E_F/k_B$ .
- Electrons at  $T = 0 \,\mathrm{K}$  still move very quickly (approximately 0.06 the speed of light) since they're quantum particles (not classical ones).
- 3D density of states:
  - The density of states g(E) is the number of one-electron states (including spin multiplicity) per unit energy and volume:

$$g(E)_{3D} \equiv \frac{1}{V} \frac{\mathrm{d}N}{\mathrm{d}E}$$

- $\blacksquare$  N is twice the product of the Fermi sphere volume and the number of levels per unit volume.
- Thus,

$$N = 2 \times \frac{4}{3}\pi k^3 \times \frac{V}{8\pi^3} = \frac{V}{3\pi^2\hbar^3} (2m^*E)^{3/2}$$

so

$$g(E)_{3D} = \frac{1}{V} \frac{dN}{dE} = \frac{1}{2\pi^2} \left(\frac{2m^*}{\hbar^2}\right)^{3/2} \sqrt{E}$$

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